

Session WE3C

Active Device Modeling

Chairman:

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TRW

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This session provides novel active parameter extraction and modeling techniques for small and large signal models. Two papers present bias and temperature dependence of the equivalent circuit parameters. The final paper presents scaling of HBT device models.

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1:30 p.m.-3:00 p.m., Wednesday, May 17, 1995
Room 12A,B,C